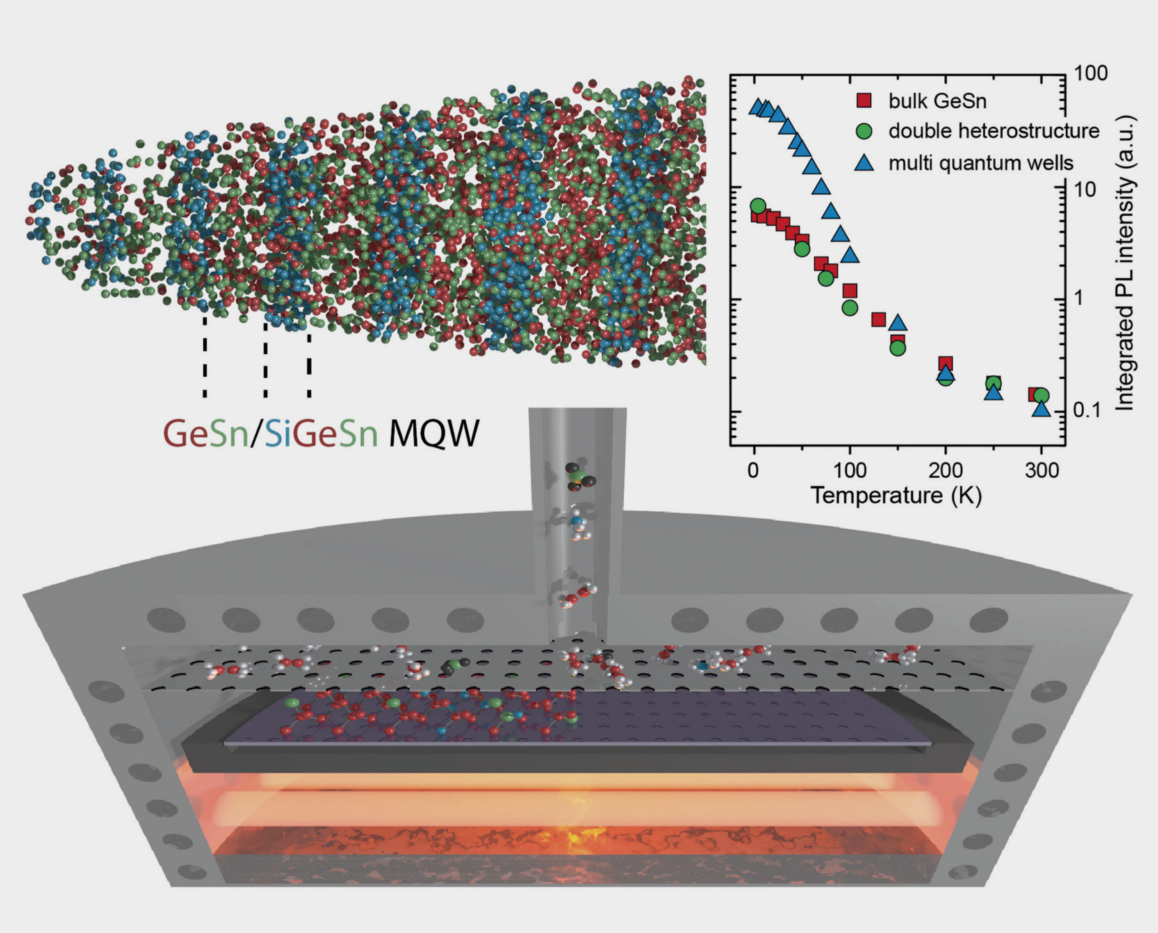

# Epitaxy of group IV Si-Ge-Sn alloys for advanced heterostructure light emitters

Nils von den Driesch

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